

## Automotive ultrafast recovery - high voltage diode

Datasheet – production data

### Features

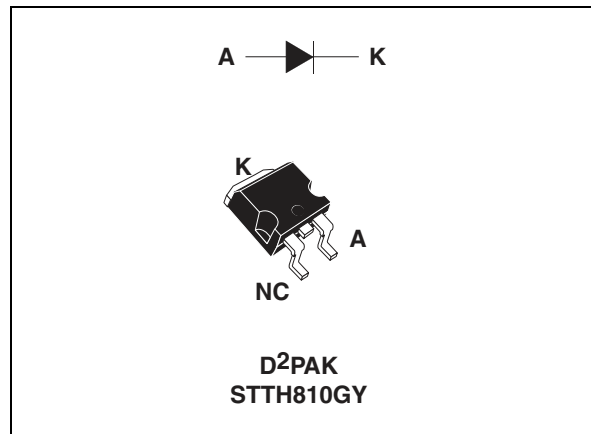
- AEC-Q101 qualified
- Ultrafast, soft recovery
- Very low conduction and switching losses
- High frequency and/or high pulsed current operation
- High reverse voltage capability
- High junction temperature

### Description

The high quality design of this diode has produced a device with low leakage current, regularly reproducible characteristics and intrinsic ruggedness. These characteristics make it ideal for heavy duty applications that demand long term reliability like automotive applications.

These diodes also fit into auxiliary functions such as snubber, bootstrap, and demagnetization applications.

The improved performance in low leakage current, and therefore thermal runaway guard band, is an immediate competitive advantage for this device.



**Table 1. Device summary**

$I_{F(AV)}$	8 A
$V_{RRM}$	1000 V
$T_j$	175 °C
$V_F$ (typ)	1.30 V
$t_{rr}$ (typ)	47 ns

# 1 Characteristics

**Table 2. Absolute ratings (limiting values at 25 °C, unless otherwise specified)**

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage	1000	V
$I_{F(RMS)}$	Forward rms current	30	A
$I_{F(AV)}$	Average forward current, $\delta = 0.5$	$T_c = 130\text{ °C}$ 8	A
$I_{FRM}$	Repetitive peak forward current	$t_p = 5\ \mu\text{s}$ , $F = 5\ \text{kHz}$ square	100 A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10\ \text{ms}$ sinusoidal	60 A
$T_{stg}$	Storage temperature range	-65 to + 175	°C
$T_j$	Operating junction temperature range	-40 to +175	°C

**Table 3. Thermal parameters**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction to case	2.5	°C/W

**Table 4. Static electrical characteristics**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25\text{ °C}$	$V_R = V_{RRM}$		5	$\mu\text{A}$
		$T_j = 125\text{ °C}$			20	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25\text{ °C}$	$I_F = 8\ \text{A}$		2	V
		$T_j = 100\text{ °C}$			1.4	
		$T_j = 150\text{ °C}$			1.7	

1. Pulse test:  $t_p = 5\ \text{ms}$ ,  $\delta < 2\%$
2. Pulse test:  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 1.3 \times I_{F(AV)} + 0.05 I_{F(RMS)}^2$$

Table 5. Dynamic characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$I_F = 1\text{ A}$ , $di_F/dt = -50\text{ A}/\mu\text{s}$ , $V_R = 30\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$		64	85	ns
		$I_F = 1\text{ A}$ , $di_F/dt = -100\text{ A}/\mu\text{s}$ , $V_R = 30\text{ V}$ , $T_j = 25\text{ }^\circ\text{C}$		47	65	
$I_{RM}$	Reverse recovery current	$I_F = 8\text{ A}$ , $di_F/dt = -200\text{ A}/\mu\text{s}$ , $V_R = 600\text{ V}$ , $T_j = 125\text{ }^\circ\text{C}$		12	16	A
S	Softness factor	$I_F = 8\text{ A}$ , $di_F/dt = -200\text{ A}/\mu\text{s}$ , $V_R = 600\text{ V}$ , $T_j = 125\text{ }^\circ\text{C}$		2		
$t_{fr}$	Forward recovery time	$I_F = 8\text{ A}$ , $di_F/dt = 50\text{ A}/\mu\text{s}$ $V_{FR} = 1.5 \times V_{Fmax}$ , $T_j = 25\text{ }^\circ\text{C}$			300	ns
$V_{FP}$	Forward recovery voltage	$I_F = 8\text{ A}$ , $di_F/dt = 50\text{ A}/\mu\text{s}$ , $T_j = 25\text{ }^\circ\text{C}$		5.5		V

Figure 1. Conduction losses versus average current

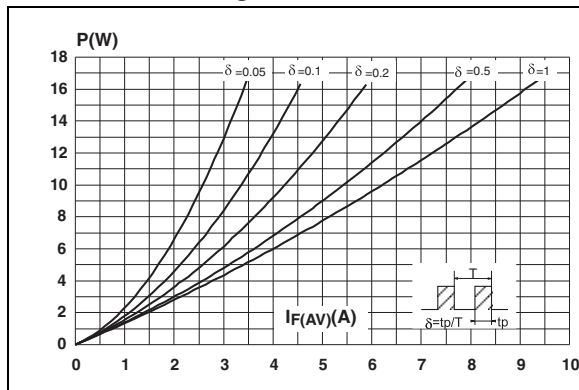


Figure 2. Forward voltage drop versus forward current

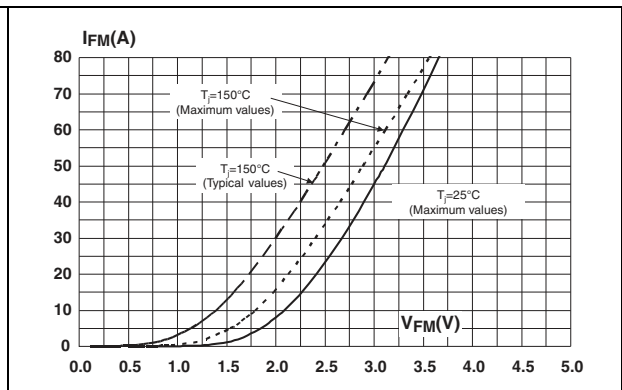


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

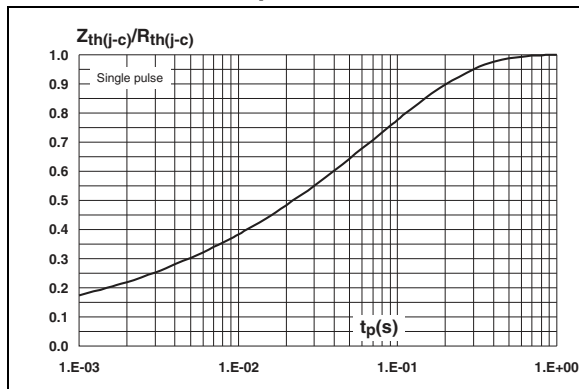


Figure 4. Peak reverse recovery current versus diF/dt (typical values)

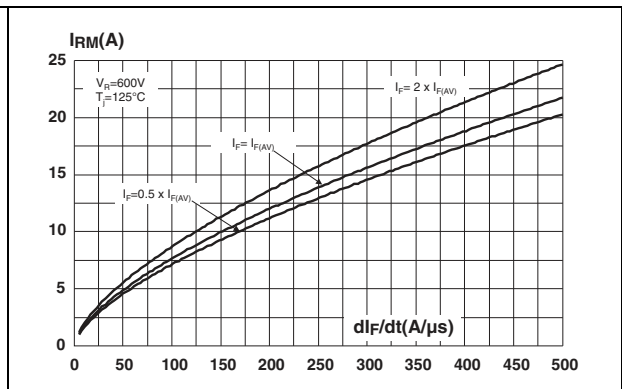


Figure 5. Reverse recovery time versus  $di_F/dt$  (typical values)

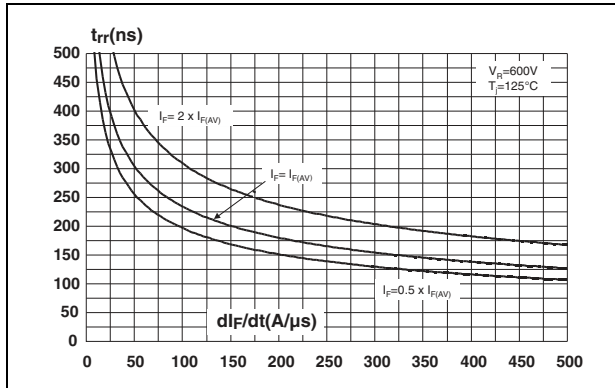


Figure 6. Reverse recovery charges versus  $di_F/dt$  (typical values)

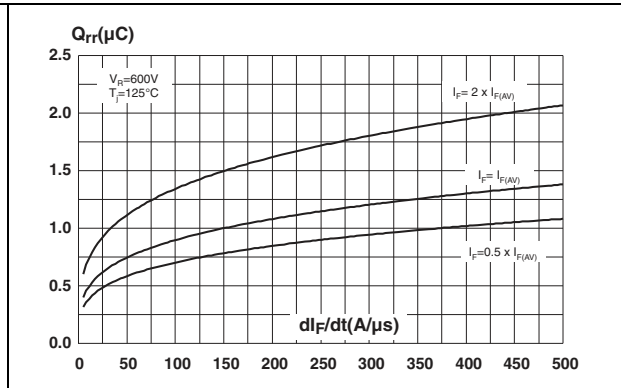


Figure 7. Softness factor versus  $di_F/dt$  (typical values)

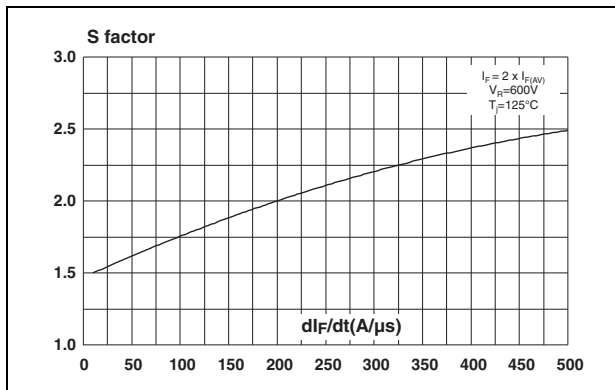


Figure 8. Relative variations of dynamic parameters versus junction temperature

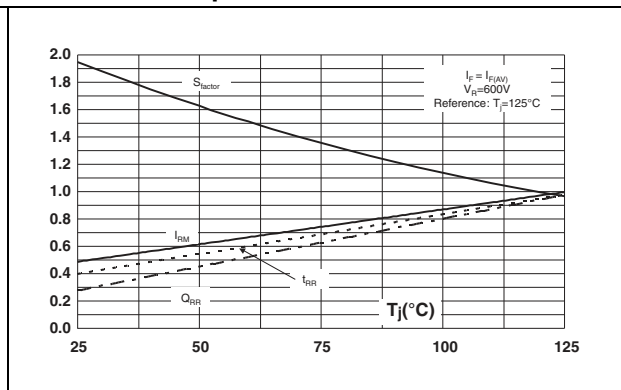


Figure 9. Transient peak forward voltage versus  $di_F/dt$  (typical values)

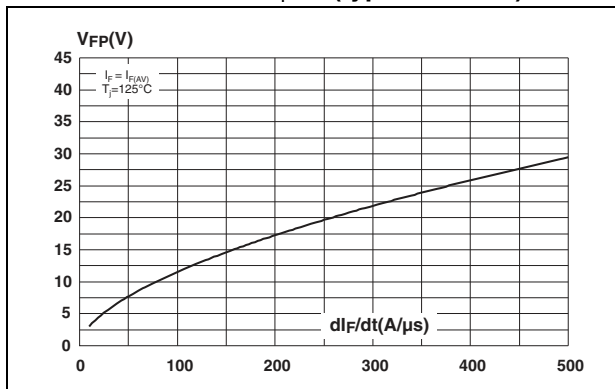


Figure 10. Forward recovery time versus  $di_F/dt$  (typical values)

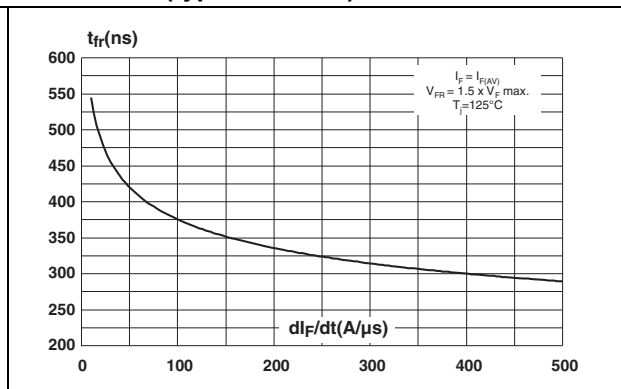


Figure 11. Junction capacitance versus reverse voltage applied (typical values)

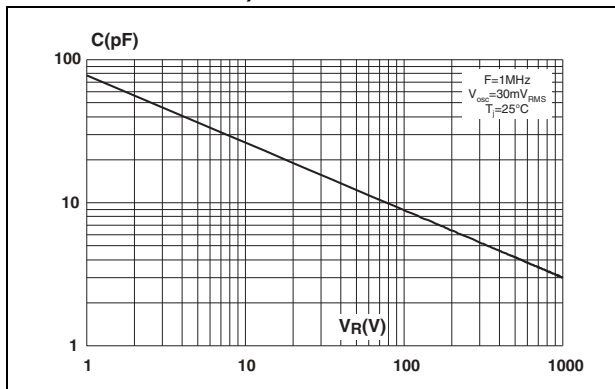
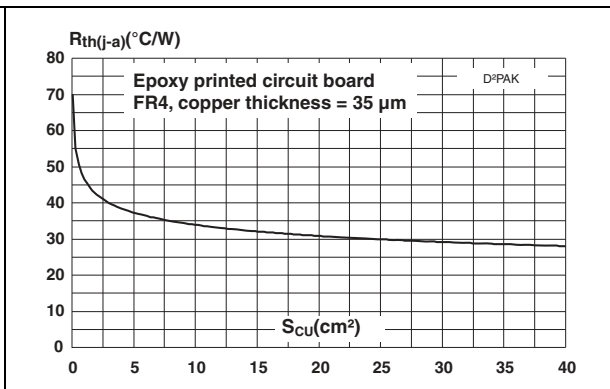


Figure 12. Thermal resistance junction to ambient versus copper surface under tab



## 2 Package information

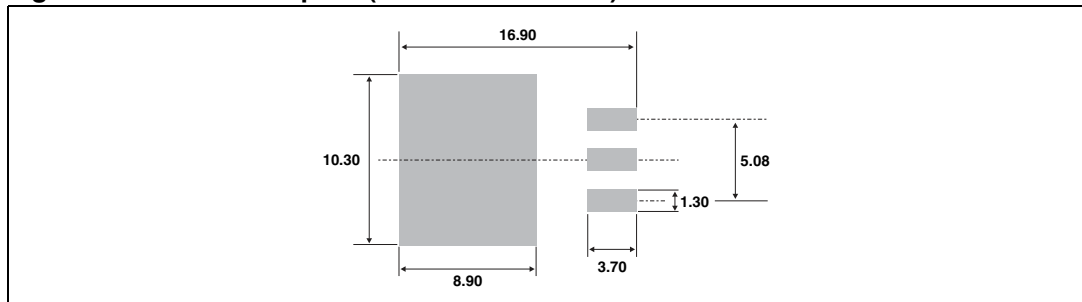
- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

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Table 6. D<sup>2</sup>PAK dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.49	2.69	0.098	0.106
A2	0.03	0.23	0.001	0.009
B	0.70	0.93	0.027	0.037
B2	1.14	1.70	0.045	0.067
C	0.45	0.60	0.017	0.024
C2	1.23	1.36	0.048	0.054
D	8.95	9.35	0.352	0.368
E	10.00	10.40	0.393	0.409
G	4.88	5.28	0.192	0.208
L	15.00	15.85	0.590	0.624
L2	1.27	1.40	0.050	0.055
L3	1.40	1.75	0.055	0.069
M	2.40	3.20	0.094	0.126
R	0.40 typ.		0.016 typ.	
V2	0°	8°	0°	8°

Figure 13. D<sup>2</sup>PAK footprint (dimensions in mm)



### 3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH810GY-TR	STTH810GY	D <sup>2</sup> PAK	1.48 g	1000	Tape & reel

### 4 Revision history

Table 8. Document revision history

Date	Revision	Changes
24-Oct-2012	1	First issue.

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